

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## **BT151S-500R-MS**

**Product specification**

## FEATURES

- Glass-passivated mesa chip for reliability and uniform
- High current output up to 12A

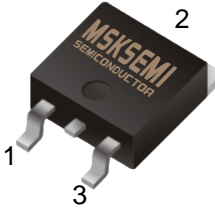
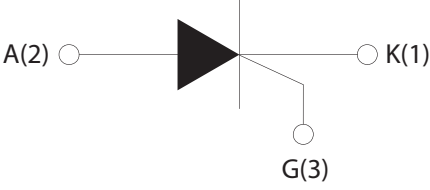

## APPLICATIONS

- Motor cycle
- Power charger
- T-tools etc

## APPROVALS

- RoHS: Compliance with
- HF: Compliance with

## Reference News

TO-252	Schematic Symbol	MARKING
		

## ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{DRM}}$	600	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{RRM}}$	600	
RMS on-state current ( $T = 110^\circ\text{C}$ )	$I_{\text{T(RMS)}}$	12	A
Non repetitive surge peak on-state current ( $t_p=10\text{ms}$ )	$I_{\text{TSM}}$	140	
$I_2t$ value for fusing ( $t_p=10\text{ms}$ )	$I_2t$	98	A <sup>2</sup> S
Critical rate of rise of on-state current ( $I_G=2 \cdot I_{\text{GT}}$ )	$d_i/d_t$	50	A/ $\mu\text{s}$
Peak gate current	$I_{\text{GM}}$	4	A
Average gate power dissipation	$P_{\text{G(AV)}}$	1	W
Storage junction temperature range	$T_{\text{STG}}$	-40~+150	°C
Operating junction temperature range	$T_j$	-40~+125	

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C )**

Symbol	Test Condition	Value	Unit
I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =33Ω	≤15	mA
V <sub>GT</sub>		≤1.5	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> , R <sub>L</sub> =3.3KΩ, T <sub>j</sub> =150°C	≥0.2	
I <sub>H</sub>	I <sub>T</sub> =500mA	≤50	mA
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	≤60	
dV <sub>D</sub> /dt	V <sub>D</sub> =2/3, V <sub>DRM</sub> Gate Open, T <sub>j</sub> =150°C	≥200	V/μs

**STATIC CHARACTERISTICS**

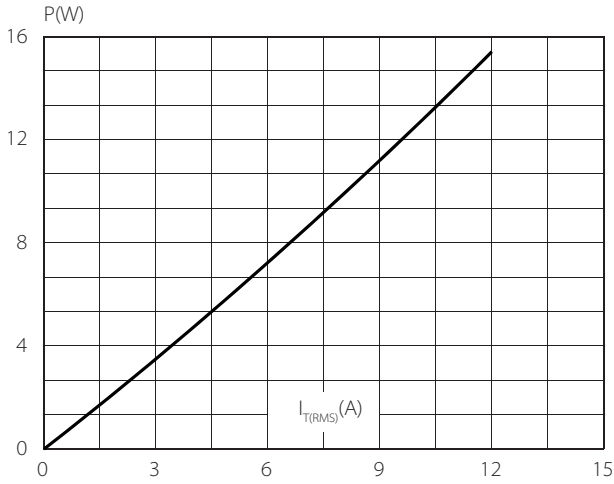
Symbol	Parameter	Value	Unit
V <sub>TM</sub>	I <sub>TM</sub> =24A, tp=380μs	≤1.55	V
I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> , V <sub>R</sub> =V <sub>RRM</sub>		
I <sub>RRM</sub>			≤2

**THERMAL RESISTANCES**

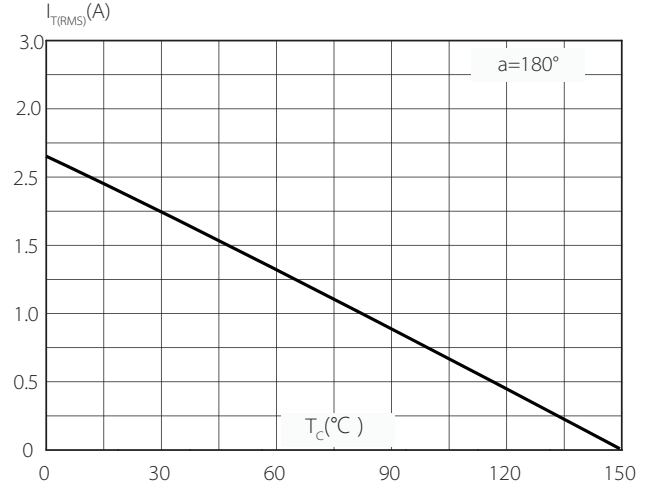
Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case(AC)	1.8	°C/W
R <sub>th(j-a)</sub>	Junction to ambient	70	°C/W

**PARAMETER CHARACTERISTIC CURVE**

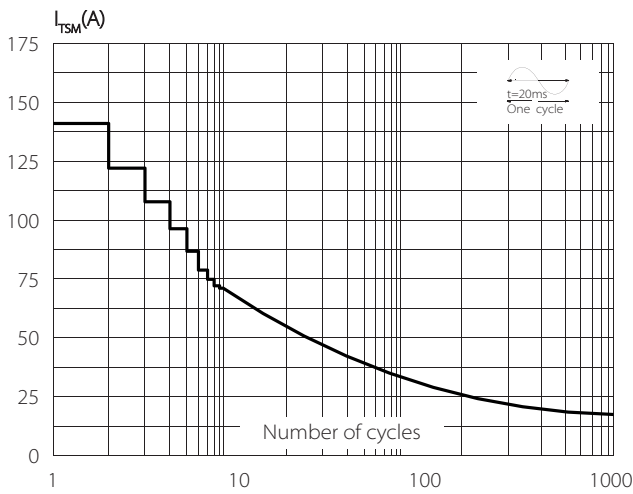
**FIG.1 Maximum power dissipation versus RMS on-state current**



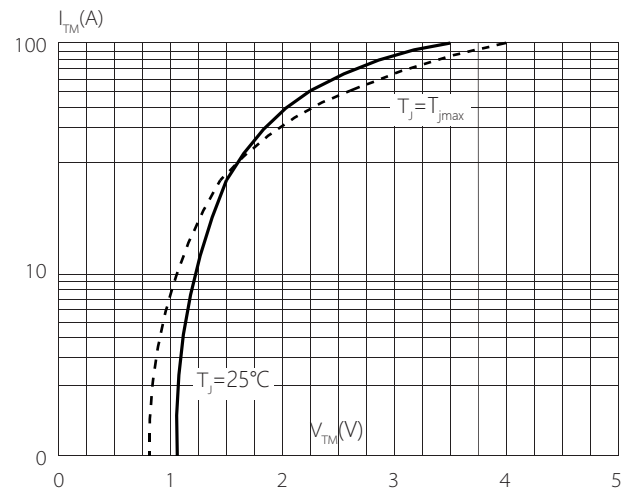
**FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)**



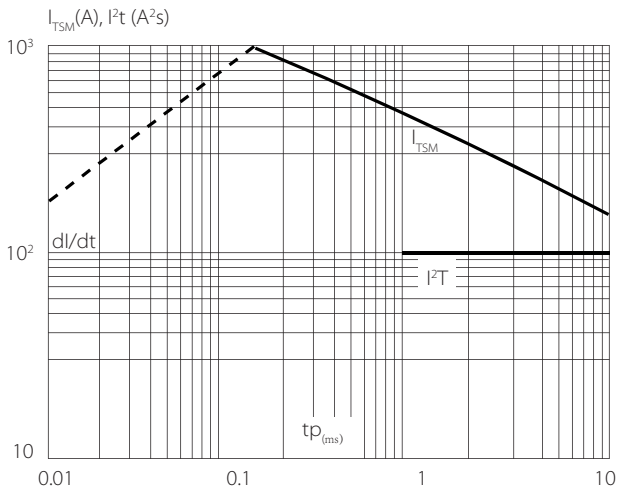
**FIG.3: Surge peak on-state current versus number of cycles**



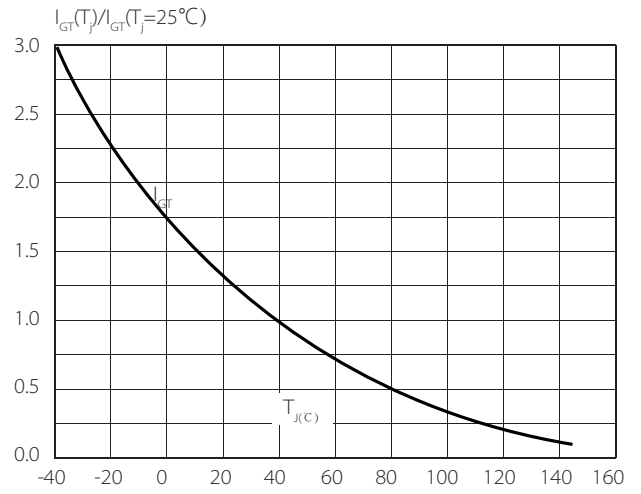
**FIG.4 On-state characteristics (maximum values)**



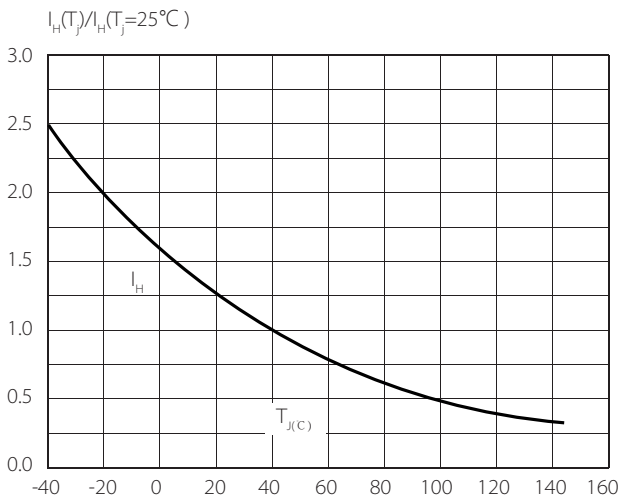
**FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$  and corresponding value of  $I^2t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )**



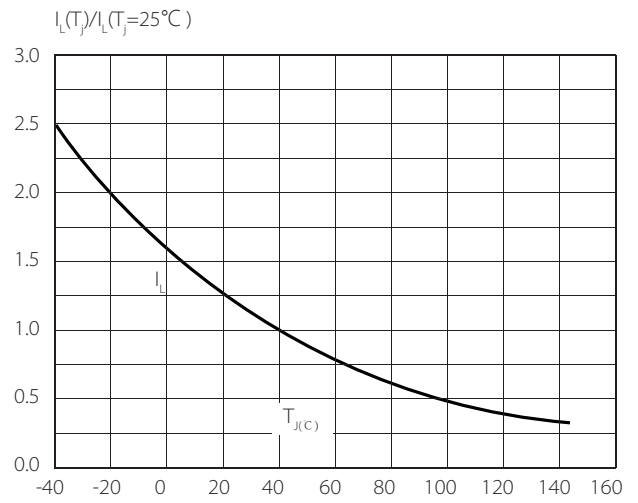
**FIG.6 Relative variations of gate trigger current, holding current and latching current versus junction temperature**



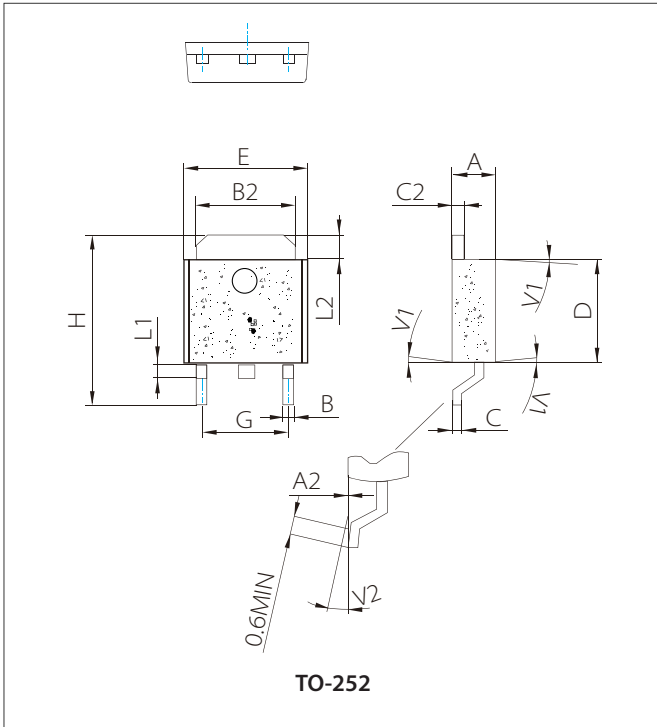
**FIG.7 Relative variations of holding current versus junction temperature**



**FIG.8 Relative variations of latching current versus junction temperature**



**PACKAGE MECHANICAL DATA**



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173	0.1	0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051	0.143	0.067
L2	1.37		1.50	0.054		0.059
L1		4°			0.130	
V2	0°		8°	0°		8°

**Order information**

P/N	PKG	QTY
BT151S-500R-MS	TO-252	2500PCS

## Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.